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February 2000

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## **FDG311N** N-Channel 2.5V Specified PowerTrench<sup>®</sup> MOSFET

## **General Description**

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance. These devices are well suited for portable electronics applications.

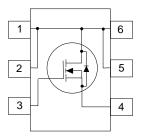
## Applications

- Load switch
- Power management
- DC/DC converter

## Features

- 1.9 A, 20 V.  $R_{DS(ON)} = 0.115 \ \Omega \ @ V_{GS} = 4.5 \ V$  $R_{DS(ON)} = 0.150 \ \Omega \ @ V_{GS} = 2.5 \ V.$
- Low gate charge (3nC typical).
- High performance trench technology for extremely low  $R_{DS(ON)}$ .
- Compact industry standard SC70-6 surface mount package.





## Absolute Maximum Ratings T<sub>A</sub> = 25 C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V <sub>DSS</sub>	Drain-Source Voltage	20	V	
V <sub>GSS</sub>	Gate-Source Voltage	±8	V	
ID	Drain Current - Continuous	(Note 1a)	1.9	A
	- Pulsed	6		
PD	Power Dissipation for Single Operation	(Note 1a)	0.75	W
		(Note 1b)	0.48	
		(	00	
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Tempera	. ,	-55 to +150	٦°
Therma	Operating and Storage Junction Tempera	ture Range		°C/W
Therma R <sub>aJA</sub> Packag	I Characteristics	ture Range	-55 to +150	

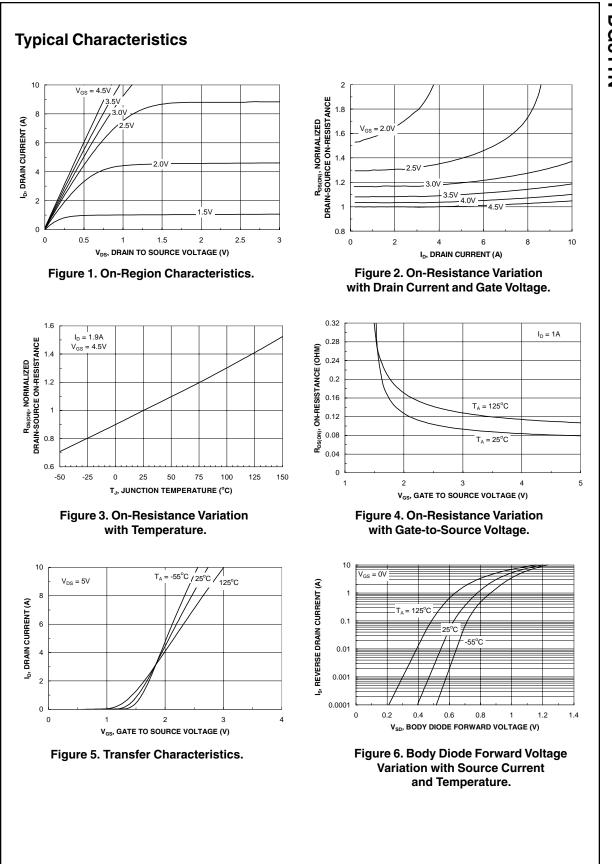
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tics source Breakdown Voltage own Voltage Temperature ient ate Voltage Drain Current ody Leakage Forward ody Leakage Reverse tics (Note 2) hreshold Voltage hreshold Voltage rature Coefficient Drain-Source sistance te Drain Current d Transconductance	$\begin{array}{l} V_{GS}=0 \; V, \; I_{D}=250 \; \mu A \\ \\ I_{D}=250 \; \mu A, \; Referenced \; to \; 25^{\circ}C \\ \\ V_{DS}=16 \; V, \; V_{GS}=0 \; V \\ \\ V_{GS}=8 \; V, \; V_{DS}=0 \; V \\ \\ V_{GS}=-8 \; V, \; V_{DS}=0 \; V \\ \\ \end{array}$	0.4	0.9 -3 0.082	1 100 -100 1.5 0.115	V mV/°C μA nA nA V mV/°C
Source Breakdown Voltage own Voltage Temperature ient ate Voltage Drain Current ody Leakage Forward ody Leakage Reverse tiCS (Note 2) hreshold Voltage hreshold Voltage rature Coefficient Drain-Source sistance	$\begin{split} I_D &= 250 \; \mu\text{A}, \; \text{Referenced to } 25^\circ\text{C} \\ V_{DS} &= 16 \; \text{V}, \; \text{V}_{GS} = 0 \; \text{V} \\ V_{GS} &= 8 \; \text{V}, \; \text{V}_{DS} = 0 \; \text{V} \\ V_{GS} &= -8 \; \text{V}, \; \text{V}_{DS} = 0 \; \text{V} \\ \end{split} \\ \end{split} \\ \begin{split} V_{DS} &= V_{GS}, \; I_D &= 250 \; \mu\text{A} \\ I_D &= 250 \; \mu\text{A}, \; \text{Referenced to } 25^\circ\text{C} \\ \hline V_{GS} &= 4.5 \; \text{V}, \; \; I_D = 1.9 \; \text{A} \\ V_{GS} &= 4.5 \; \text{V}, \; \; I_D = 1.9 \; \text{A}, \\ T_J &= 125^\circ\text{C} \\ V_{GS} &= 2.5 \; \text{V}, \; \; I_D = 1.6 \; \text{A} \end{split}$		0.9 -3 0.082	100 -100 1.5	mV/°C μA nA nA V mV/°C
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sistance te Drain Current	$ \begin{array}{ll} V_{GS} = 4.5 \; V, & I_D = 1.9 \; A, \\ & T_J = 125^\circ C \\ V_{GS} = 2.5 \; V, & I_D = 1.6 \; A \end{array} $			0.115	0
	VG3 = 2.0 V, ID = 1.0 / (		0.110	0.170	Ω
d Transcanductonco	$V_{GS} = 4.5 V, V_{DS} = 5 V$	4			A
u Transconductance	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 0.5 A		6		S
cteristics					
	$V_{DS} = 10 V, V_{GS} = 0 V,$		270		pF
Capacitance	f = 1.0 MHz		55		pF
e Transfer Capacitance	-		20		pF
acteristics (Note 2)					
	$V_{DD} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ A}, \\ V_{GS} = 5 \text{ V}, \text{ R}_{GEN} = 6 \Omega$		5	12	ns
n Rise Time			9	17	ns
ff Delay Time	1		10	18	ns
ff Fall Time	1		2	6	ns
ate Charge	$V_{DS} = 10 \text{ V}, I_D = 1.9 \text{ A}, V_{GS} = 4.5 \text{ V}$		3	4.5	nC
ource Charge			0.6		nC
rain Charge			0.9		nC
iode Characteristics	and Maximum Ratings				
				0.42	A
	$V_{GS} = 0 V, I_S = 0.42 A$ (Note 2)		0.7	1.2	V
	apacitance Capacitance e Transfer Capacitance acteristics (Note 2) n Delay Time n Rise Time ff Delay Time ff Fall Time ate Charge ource Charge rain Charge iode Characteristics um Continuous Drain-Source source Diode Forward	apacitance $V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$ Capacitancef = 1.0 MHze Transfer Capacitancef = 1.0 MHzacteristics (Note 2)nn Delay Time $V_{DD} = 10 \text{ V}, \text{ I}_D = 1 \text{ A},$ N Rise Time $V_{DS} = 5 \text{ V}, \text{ R}_{GEN} = 6 \Omega$ ff Delay Time $V_{DS} = 10 \text{ V}, \text{ I}_D = 1.9 \text{ A},$ ff Fall Time $V_{DS} = 10 \text{ V}, \text{ I}_D = 1.9 \text{ A},$ ource Charge $V_{DS} = 4.5 \text{ V}$ rain ChargeVersent Currentiode Characteristics and Maximum Ratingsum Continuous Drain-Source Diode Forward Currentsource Diode Forward $V_{GS} = 0 \text{ V}, \text{ I}_S = 0.42 \text{ A}$ (Note 2)	apacitance $V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$ Capacitance       f = 1.0 MHz         e Transfer Capacitance       f = 1.0 MHz         acteristics       (Note 2)         n Delay Time $V_{DD} = 10 \text{ V}, \text{ I}_D = 1 \text{ A},$ n Rise Time $V_{GS} = 5 \text{ V}, \text{ R}_{GEN} = 6 \Omega$ ff Delay Time $V_{DS} = 10 \text{ V}, \text{ I}_D = 1.9 \text{ A},$ ource Charge $V_{GS} = 4.5 \text{ V}$ rain Charge $V_{GS} = 0 \text{ V}, \text{ I}_S = 0.42 \text{ A}$ iode Characteristics and Maximum Ratings         um Continuous Drain-Source Diode Forward Current         source Diode Forward $V_{GS} = 0 \text{ V}, \text{ I}_S = 0.42 \text{ A}$ (Note 2)	apacitance $V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz270Capacitancef = 1.0 MHz55e Transfer Capacitance20acteristics (Note 2)(Note 2)n Delay Time $V_{DD} = 10 \text{ V}, \text{ I}_D = 1 \text{ A},$ $V_{GS} = 5 \text{ V}, \text{ R}_{GEN} = 6 \Omega$ 9ff Delay Time10ff Fall Time2ate Charge $V_{DS} = 10 \text{ V}, \text{ I}_D = 1.9 \text{ A},$ $V_{GS} = 4.5 \text{ V}$ 3ource Charge0.9iode Characteristics and Maximum Ratingsum Continuous Drain-Source Diode Forward Current0.9iource Diode Forward $V_{GS} = 0 \text{ V}, \text{ I}_S = 0.42 \text{ A}$ (Note 2)0.7	apacitance $V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz270Capacitancef = 1.0 MHz55e Transfer Capacitance20acteristics (Note 2)n Delay Time $V_{DD} = 10 \text{ V}, \text{ I}_D = 1 \text{ A},$ $V_{GS} = 5 \text{ V}, \text{ R}_{GEN} = 6 \Omega$ n Rise Time10ff Delay Time10ff Fall Time2ate Charge $V_{DS} = 10 \text{ V}, \text{ I}_D = 1.9 \text{ A},$ $V_{GS} = 4.5 \text{ V}$ ource Charge0.6rain Charge0.9iode Characteristics and Maximum Ratingsum Continuous Drain-Source Diode Forward Current0.42source Diode Forward $V_{GS} = 0 \text{ V}, \text{ I}_S = 0.42 \text{ A}$ (Note 2)0.7t-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface

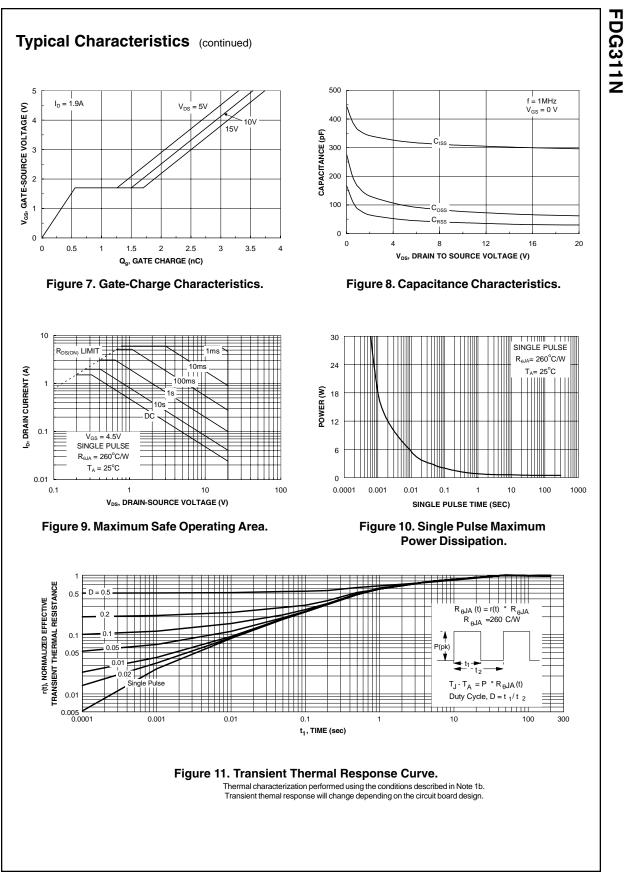
2. Pulse Test: Pulse Width  $\leq$  300  $\mu s,$  Duty Cycle  $\leq$  2.0%

FDG311N Rev. D

FDG311N



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